

## 2SK1318

Silicon N Channel MOS FET  
High Speed Power Switching

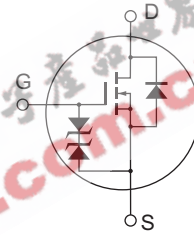
REJ03G0930-0200  
(Previous: ADE-208-1269)  
Rev.2.00  
Sep 07, 2005

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

### Outline

RENESAS Package code: PRSS0003AD-A  
(Package name: TO-220FM)



1. Gate
2. Drain
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	120	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	20	A
Drain peak current	I <sub>D (peak)</sub> <sup>*1</sup>	80	A
Body to drain diode reverse drain current	I <sub>DR</sub>	20	A
Channel dissipation	P <sub>ch</sub> <sup>*2</sup>	35	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at Tc = 25°C

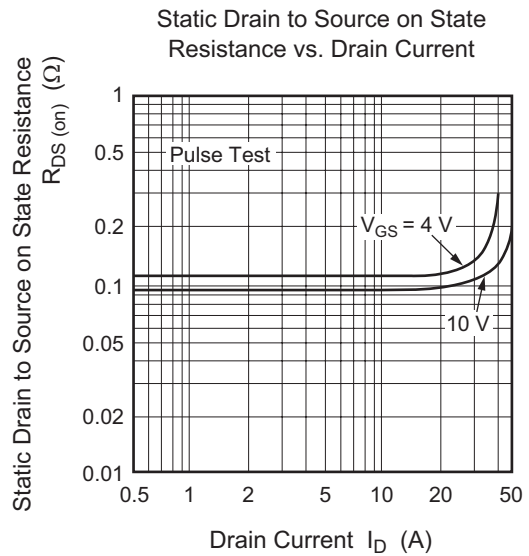
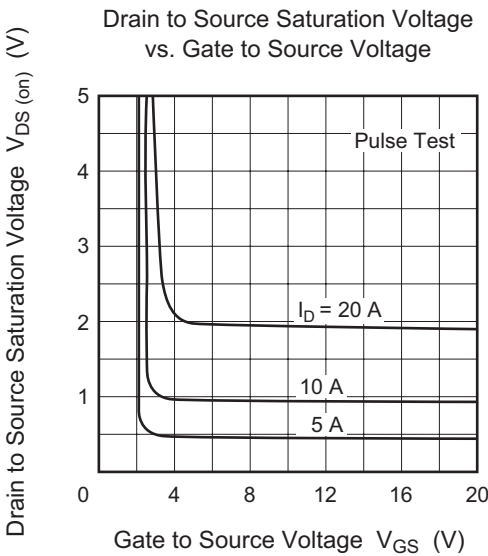
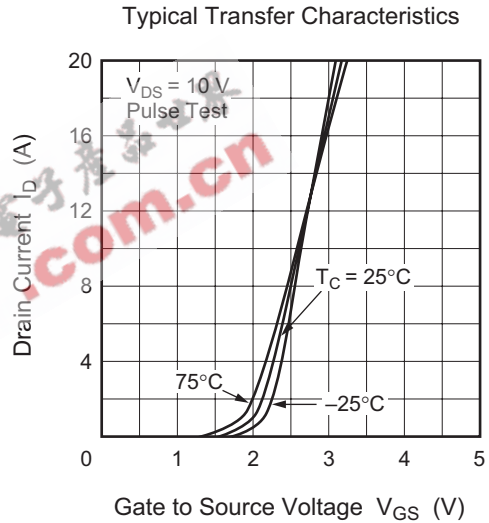
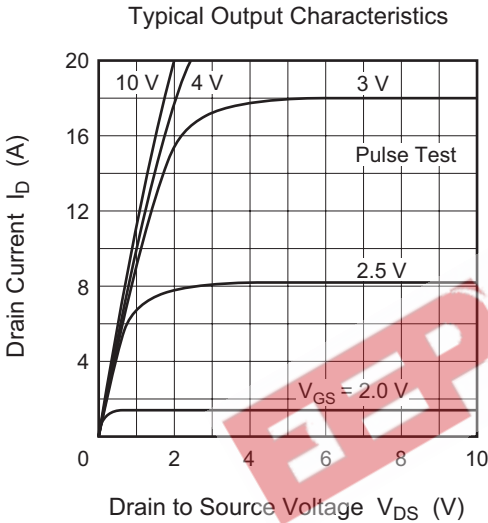
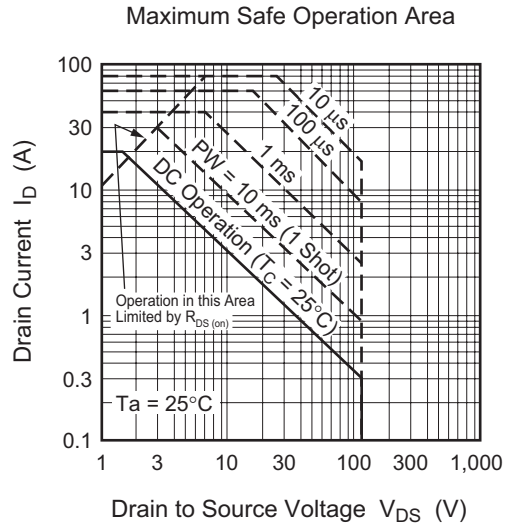
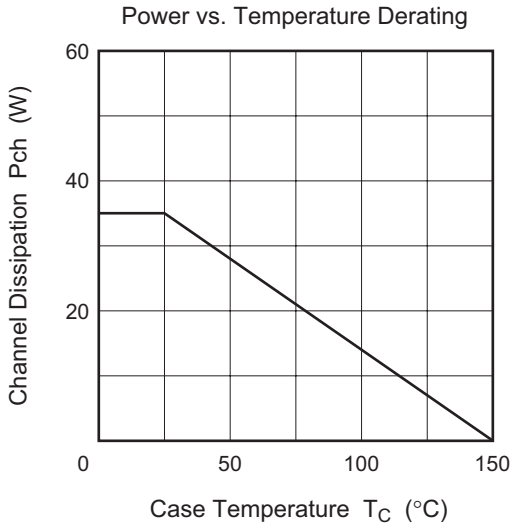
## Electrical Characteristics

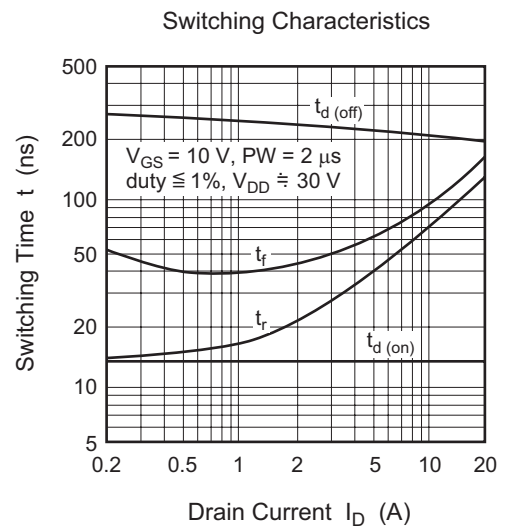
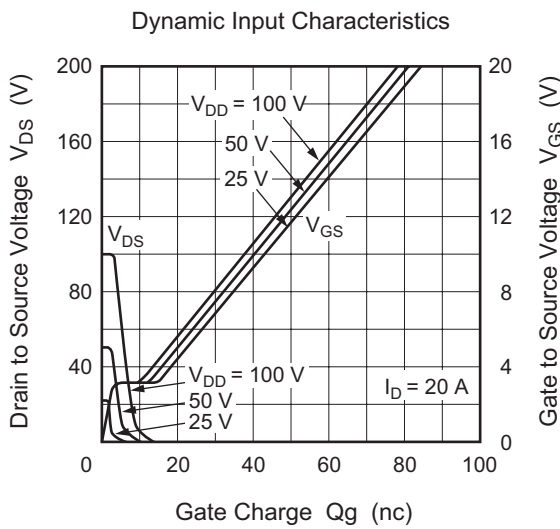
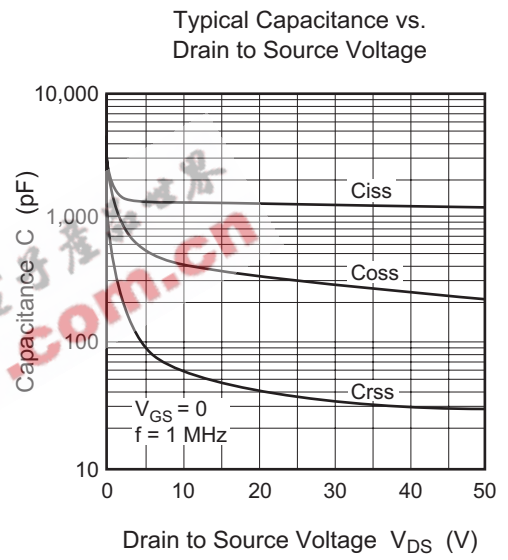
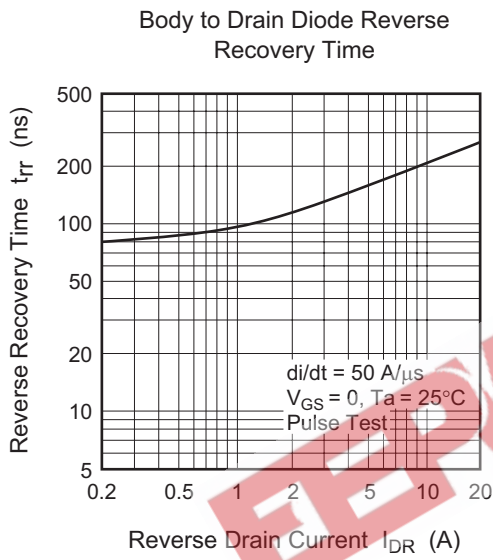
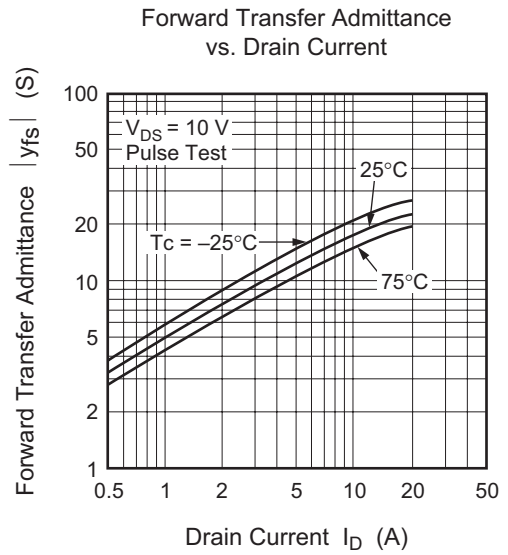
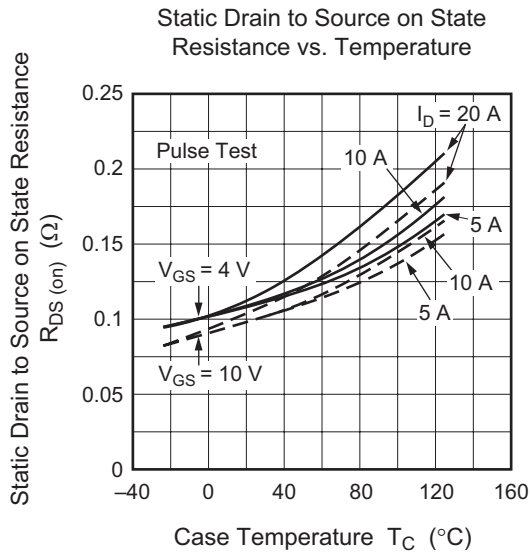
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	120	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	μA	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0	—	2.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.095	0.12	Ω	I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V <sup>*3</sup>
		—	0.11	0.16	Ω	I <sub>D</sub> = 10 A, V <sub>GS</sub> = 4 V <sup>*3</sup>
Forward transfer admittance	y <sub>fs</sub>	10	17	—	S	I <sub>D</sub> = 10 A, V <sub>DS</sub> = 10 V <sup>*3</sup>
Input capacitance	C <sub>iss</sub>	—	1300	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	430	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	60	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	14	—	ns	I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V, R <sub>L</sub> = 3 Ω
Rise time	t <sub>r</sub>	—	70	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	210	—	ns	
Fall time	t <sub>f</sub>	—	90	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	1.4	—	V	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	280	—	ns	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0, di <sub>F</sub> / dt = 50 A / μs

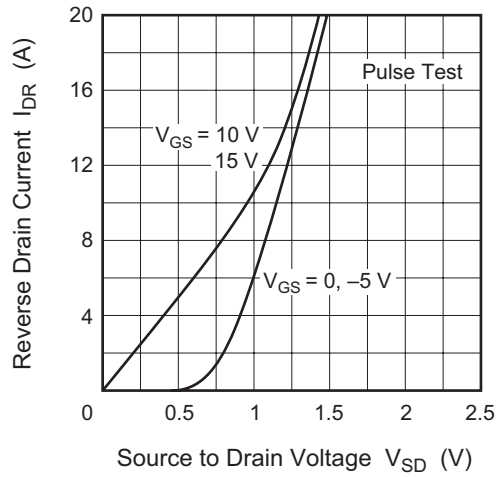
Note: 3. Pulse test

Main Characteristics

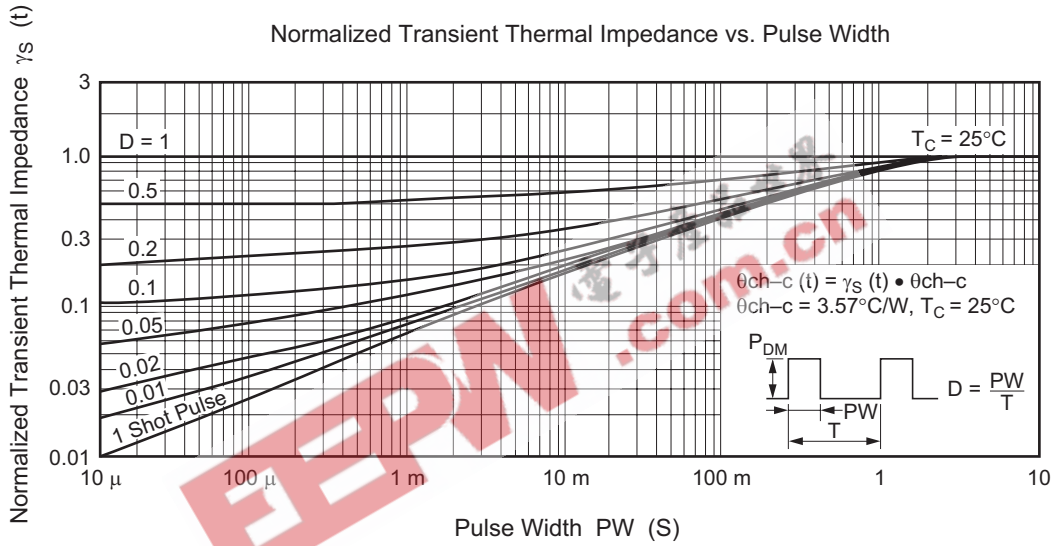




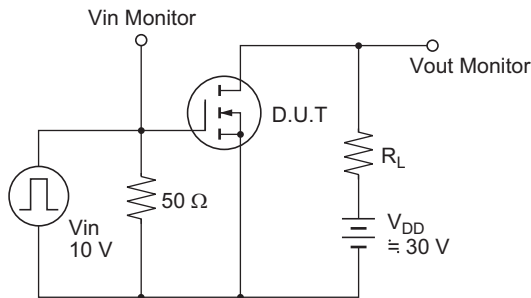
Reverse Drain Current vs. Source to Drain Voltage



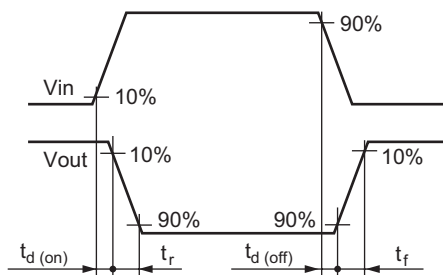
Normalized Transient Thermal Impedance vs. Pulse Width



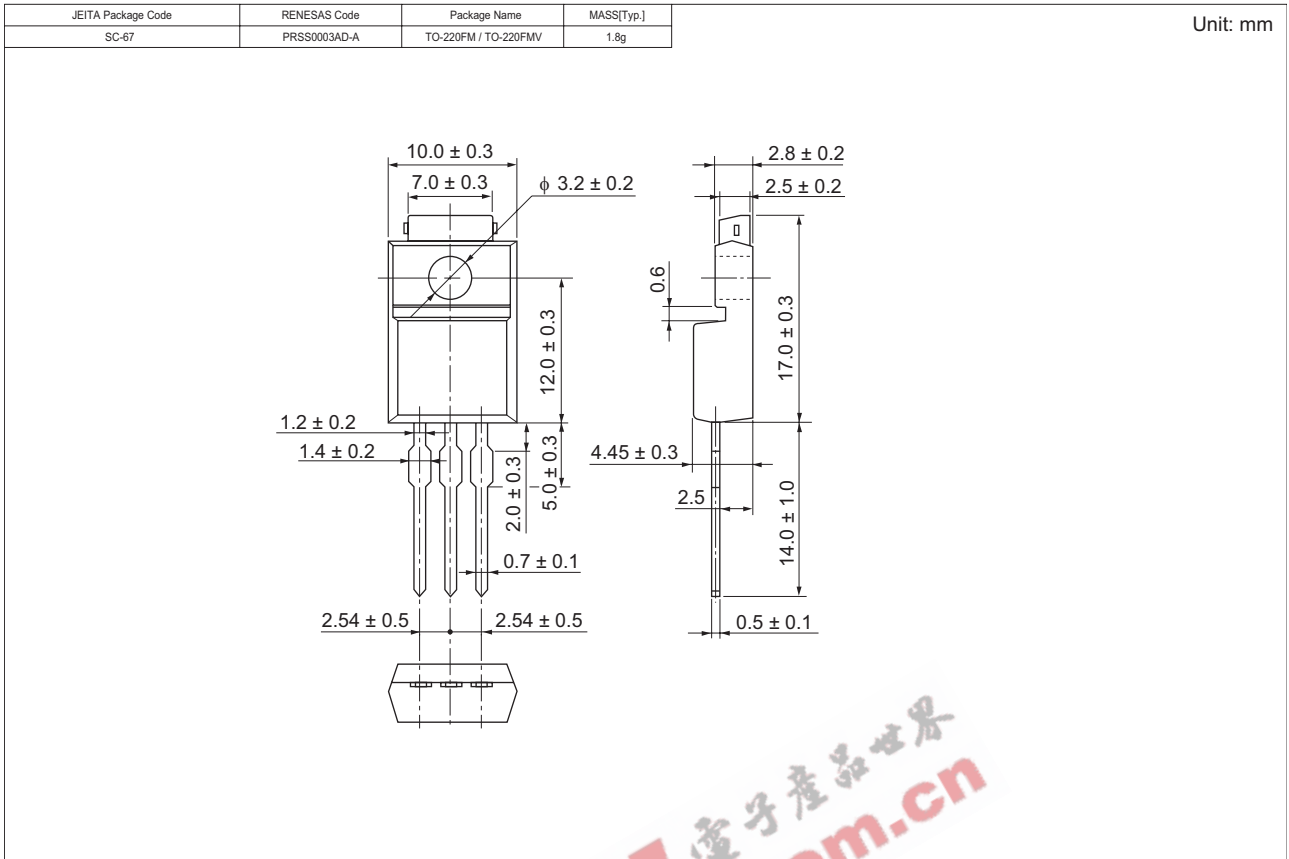
Switching Time Test Circuit



Waveforms



### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SK1318-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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